



### P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	RDS(ON) Max	I <sub>D</sub> T <sub>A</sub> = +25°C	
-40V	$11m\Omega$ @ $V_{GS} = -10V$	-11.4A	
	15mΩ @ V <sub>GS</sub> = -4.5V	-9.8A	

### **Description**

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

## **Applications**

- **DC-DC Converters**
- **Power Management Functions**
- Analog Switch

## **Features and Benefits**

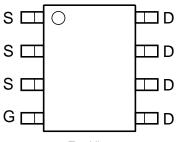
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production Low On-Resistance
- Low Input Capacitance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMPH4015SSQ)

### Mechanical Data

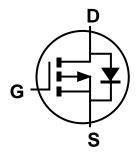
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.074 grams (Approximate)











**Equivalent Circuit** 

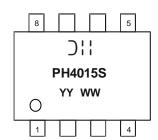
### Ordering Information (Note 4)

Part Number	Case	Packaging
DMPH4015SSS-13	SO-8	2,500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



⊃¦¦ = Manufacturer's Marking PH4015S = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 16 = 2016) WW = Week (01 to 53)



## **Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	-40	V
Gate-Source Voltage			V <sub>GSS</sub>	±25	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$	I <sub>D</sub>	-11.4 -8.1	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	-85	Α
Maximum Body Diode Continuous Current (Note 6)			Is	-3	Α
Avalanche Current (Note 7) L = 1mH			I <sub>AS</sub>	-22	Α
Avalanche Energy (Note 7) L = 1mH			E <sub>AS</sub>	260	mJ

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	1.4	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	90	°C/W
Total Power Dissipation (Note 6)	P <sub>D</sub>	1.8	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	70	°C/W
Thermal Resistance, Junction to Case (Note 6)	R <sub>θJC</sub>	7.0	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

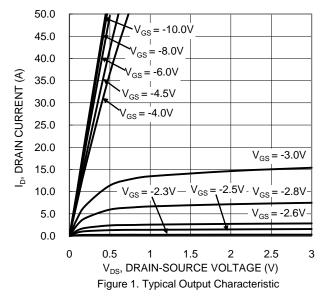
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)	1 0 7		- 71-				
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-40	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1	μΑ	$V_{DS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.5	_	-2.5	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance		_	9	11	mΩ	$V_{GS} = -10V, I_D = -9.8A$	
Static Dialii-Source Off-Resistance	R <sub>DS(ON)</sub>	_	11	15	11122	$V_{GS} = -4.5V$ , $I_{D} = -9.8A$	
Forward Transfer Admittance	Y <sub>fs</sub>	_	26	_	S	$V_{DS} = -20V, I_{D} = -9.8A$	
Diode Forward Voltage	V <sub>SD</sub>	_	-0.7	-1	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C <sub>iss</sub>	_	4,234			V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V f = 1MHz	
Output Capacitance	Coss	_	1,036	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	526	_			
Gate Resistance	$R_{G}$	_	7.8	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg	_	42.7	_		$V_{DS} = -20V, I_D = -9.8A$	
Total Gate Charge (V <sub>GS</sub> = -10V)	$Q_g$	_	91	_	nC		
Gate-Source Charge	Q <sub>gs</sub>	_	14.2	_	IIC		
Gate-Drain Charge	$Q_{gd}$	_	13.5	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	13.2	_		$V_{GS} = -10V$ , $V_{DD} = -20V$ , $R_G = 6\Omega$ , $I_D = -1A$ , $R_L = 20\Omega$	
Turn-On Rise Time	t <sub>R</sub>	_	10	_	no		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	303	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	138	_			
Reverse Recovery Time	t <sub>RR</sub>	_	26	_	ns	I <sub>F</sub> = -9.8A, di/dt = -100A/μs	
Reverse Recovery Charge	$Q_{RR}$	_	20	_	nC	I <sub>F</sub> = -9.8A, di/dt = -100A/µs	

Notes

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J$  = +25°C.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.





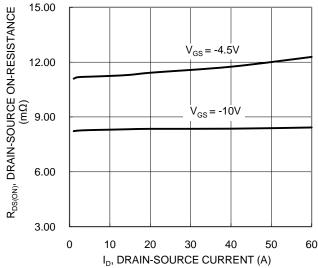


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

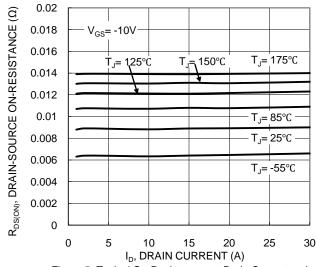
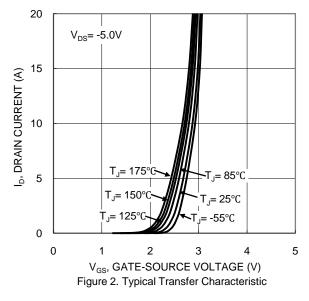
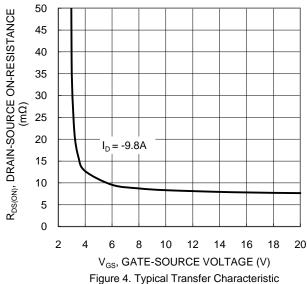


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





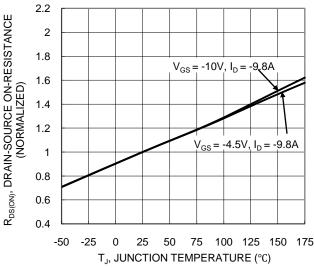


Figure 6. On-Resistance Variation with Temperature



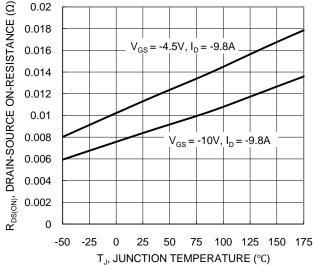
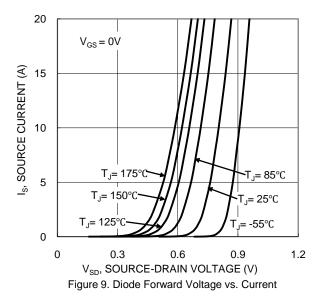
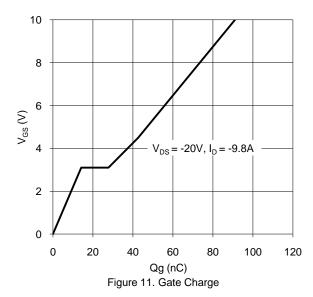


Figure 7. On-Resistance Variation with Temperature





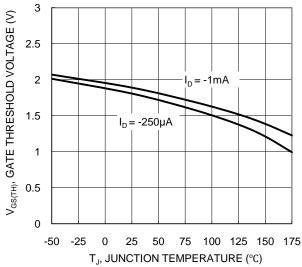
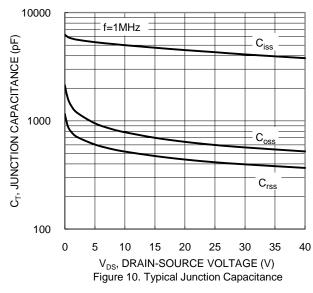
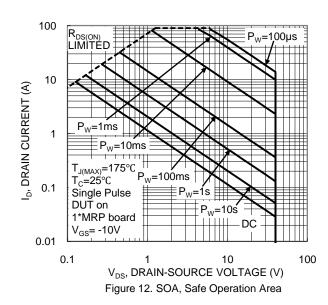


Figure 8. Gate Threshold Variation vs. Junction Temperature







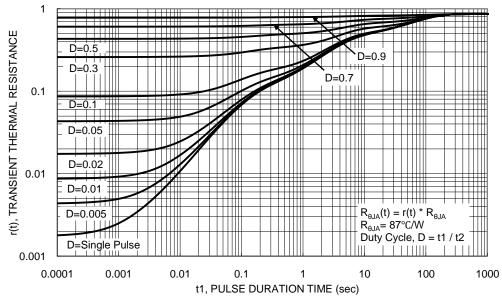


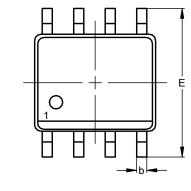
Figure 13. Transient Thermal Resistance

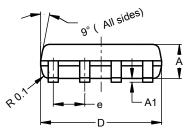


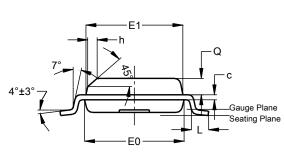
## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

**SO-8** 



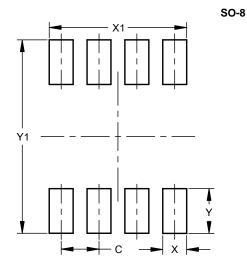




SO-8					
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A1	0.10	0.20	0.15		
b	0.30	0.50	0.40		
C	0.15	0.25	0.20		
D	4.85	4.95	4.90		
Е	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
е			1.27		
h	-		0.35		
L	0.62	0.82	0.72		
ø	0.60	0.70	0.65		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)			
С	1.27			
Х	0.802			
X1	4.612			
Υ	1.505			
Y1	6.50			

January 2017

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